

Selective Electrodesorption-Based Atomic Layer Deposition (SEBALD) of Bismuth under Morphological Control

by Walter Giurlani, Andrea Giaccherini, Emanuele Salvietti, Maurizio Passaponti, Andrea Comparini, Vittorio Morandi, Fabiola Liscio, Massimiliano Cavallini, and Massimo Innocenti

The development of next-generation electronics is very dependent on the discovery of materials with exceptional surface-state spin and valley properties. Bismuth has most of the characteristics required for technological development in this field. Thin films of this element have shown nontrivial topology¹⁻³ enabling their definition as a topological insulator and a distribution of spin states and valleys in the band diagram that are suitable for both spintronics and valleytronics applications.⁴ In some cases, these properties depend on the quantum confinement of the related particles or quasi-particles; hence they can be tuned by varying the thickness in the ultrathin film range.⁵ Finally, thin films of Bi can be processed by electrochemical lithographic methods.⁶

Bismuth ultrathin films can be obtained by techniques that require vapor phase with different degrees of vacuum (e.g., PVD and CVD).⁷⁻⁹ These methods are efficient for producing flat polycrystalline thin films of Bi. Similarly, Bi thin films were electrodeposited from an aqueous solution containing organic additives with multiple morphologies and textures according to the different surface effect promoted by these substances.¹⁰ These studies have demonstrated that Bi thin films are among the wide range of technologically interesting coatings that cannot be easily obtained from aqueous solutions without interference from metal oxide growth. In most cases, these processes lead to films with uncontrolled morphology.

Introduction to SEBALD

To avoid these limitations, we explored the possibility of using electrochemical atomic layer deposition (E-ALD) to deposit highly ordered ultrathin films from diluted aqueous solutions at room temperature and pressure. In the present context, we use E-ALD for the growth of metal chalcogenide films. Underpotential deposition (UPD) of metal chalcogenide is possible due to the energy gain involved in the formation of the corresponding chalcogenide, so that an adlayer of metal can be deposited at an underpotential on a chalcogenide

adlayer covering the electrode surface. The combination between the alternation of solutions containing precursor elements that form this type of compound and UPD is the basis of E-ALD. Repetition of the basic cycle of depositions leads to the growth of semiconductor materials whose thickness increases with the number of cycles, up to the ultrathin film range. Then, after selective electrodesorption of the chalcogen layer, the resulting film is constituted by a confined layer of metal, which reorganizes its shape in ordered crystalline domains. Therefore, the selective desorption of the chalcogen leaves an increasingly higher amount of metals with the number of cycles.

The combination of E-ALD with this second stage leads to a process called selective electrodesorption-based atomic layer deposition (SEBALD), which is depicted by the scheme in Fig. 1. SEBALD was successfully used to grow Cd with a control level not achievable in overpotential deposition through the application of Faraday's laws (even when deposition was limited to very low overpotentials)¹¹ and to obtain Co/Fe catalytic clusters.¹² In what follows, we show that with the SEBALD protocol it is possible to obtain the growth of a high-quality bismuth ultrathin film on the Ag (111) surface. In this way, we have overcome most of the problems derived from the electrochemical properties of bismuth at the solid-water electrified interface.

SEBALD of Bismuth Thin Films

As often happens in E-ALD,¹³ deposition during the first step plays a crucial role for the growth of the following layers. The first phase of SEBALD consisted of the deposition of (Se/Bi)_n on Ag, followed by the removal of selenium (Fig. 1). For this reason, the deposition conditions and the stability of the two elements were investigated first.

The deposition of Se is a well-known process described in literature.^{14,15} A selenide solution was used, and silver working electrode potential was set at -0.90 V versus Ag/AgCl sat. KCl

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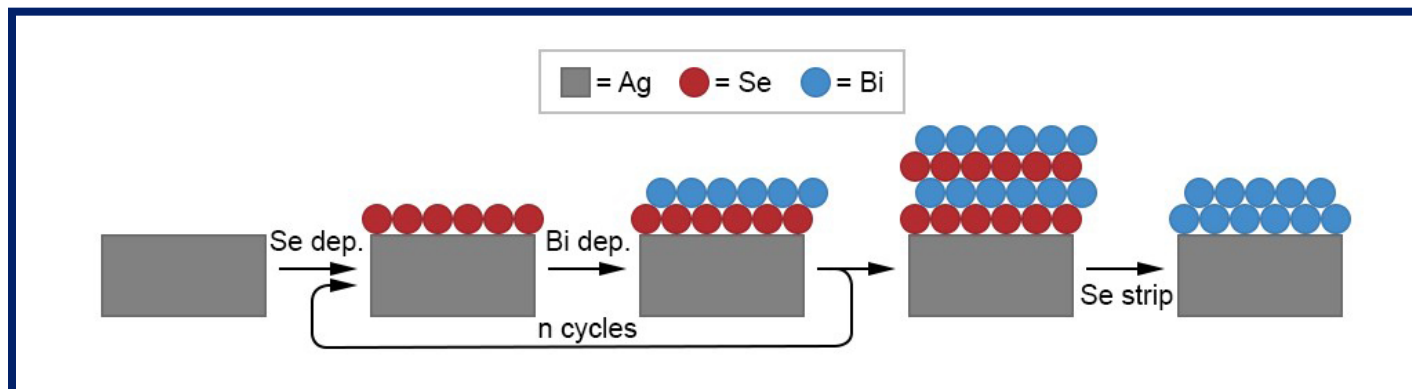


Fig. 1. Schematic operations of a SEBALD alternating a chalcogenide layer to a metal one. In our study, the chalcogenide is represented by selenium while bismuth is the metal.

reference electrode for one minute. Then, to remove the excess bulk selenium deposited, leaving only the UPD layer on silver, the working electrode was immersed in ammonia buffer solution for another minute at the same potential value. The bismuth settles to more positive potentials than selenium; therefore it is crucial for a correct E-ALD to verify the stability of Se with an anodic scan, and the results show that it does not get oxidized. Once we had ensured the stability of the Se UPD layer, we proceeded with the UPD of bismuth. The thermodynamic possibility of this deposition is justified by the presence of a cathodic peak (-0.40 – -0.50 V) slightly before the massive deposition one (over -0.50 V) in a cyclic voltammetry scan of a bismuth (III) solution (inset image in Fig. 2). After that, a conventional UPD study was carried out to evaluate the amount of metal deposited in function of the deposition potential and time.¹⁶ The optimal UPD condition to deposit bismuth on selenium consists of keeping the potential fixed at -0.43 V for one minute in the presence of the bismuth solution and then washing the sample with ammonia buffer solution.

After having optimized the UPD conditions of both the elements, the first step of SEBALD was performed by sequential automatic alternate deposition for multiple cycles, obtaining a deposit of increasing thickness. After the deposition process, SEBALD was completed by setting the working electrode potential at -2.0 V and washing the cell in the buffer solution, in order to remove all the selenium previously deposited. Anodic stripping of the remaining bismuth confirmed its growth over the number of cycles performed (Fig. 2). For the very first cycles, a typical rapid growth, due to interaction phenomena confined to the nanoscale, is present. After the fifth deposition cycle, the trend becomes linear.

A 50-cycles final bismuth deposit was morphologically characterized, revealing that this simple SEBALD process, performed at room conditions, allows obtainment of a highly ordered and crystalline deposit difficult to obtain with other techniques. From the SEM image (Fig. 3A), we can observe how the bismuth deposit obtained by SEBALD has reorganized into its typical crystalline shape,¹⁷ hard to obtain with direct bulk deposition. The EDX (Fig. 3B)

data confirm the presence of bismuth metal on the silver electrode without any traces of selenium, diagnostic of a proper SEBALD. AFM measurements (Fig. 3C) give useful information on the surface topology: the estimated RMS roughness is only 5.06 nm; moreover the image shows an overview of the sample.

Finally, the quality of the Bi thin film was quantified by XRD. The specular scan reported in Fig. 4 shows the peak of the substrate (Ag (111)) and, more importantly, peaks of Bi thin film corresponding to (102) and (204) crystalline planes. This observation indicates the growth of high-crystalline films with [102] texturing.

Conclusions and Outlook

The development of next-generation electronic devices demands specific materials that often are not simple to synthesize in the required way. SEBALD opens up the possibility of employing electrochemical processes to build, one by one, monolayers of highly pure and ordered structures. The SEBALD methodology constitutes an efficient approach to overcome the limitations of electrodepositing bismuth layers from aqueous solution. This is done by exploiting the SLRs of bismuth and selenium on Ag (111), characterized conclusively by means of electrochemical methods. The UPD experiments proved the occurrence of a SLR leading to the growth of a Bi_{ad} on Se. On this basis, multiple E-ALD cycles could be performed to grow the Bi_2Se_3 compound. Subsequent selective desorption of selenium concludes the SEBALD process and allows obtainment of the bismuth ultrathin film.

We were able to grow extremely ordered bismuth layers with exquisite control on film thickness, as proven by the topography and morphology of the resulting ultrathin films. This process is a very promising candidate for the growth of metal ultrathin films and constitutes an easy way to obtain an ordered bismuth ultrathin film of controlled thickness under room temperature and pressure. The films obtained by SEBALD are highly crystalline and oriented; moreover they are characterized by low roughness. All these properties are promising for ultimate application in new-generation electronic devices. ■

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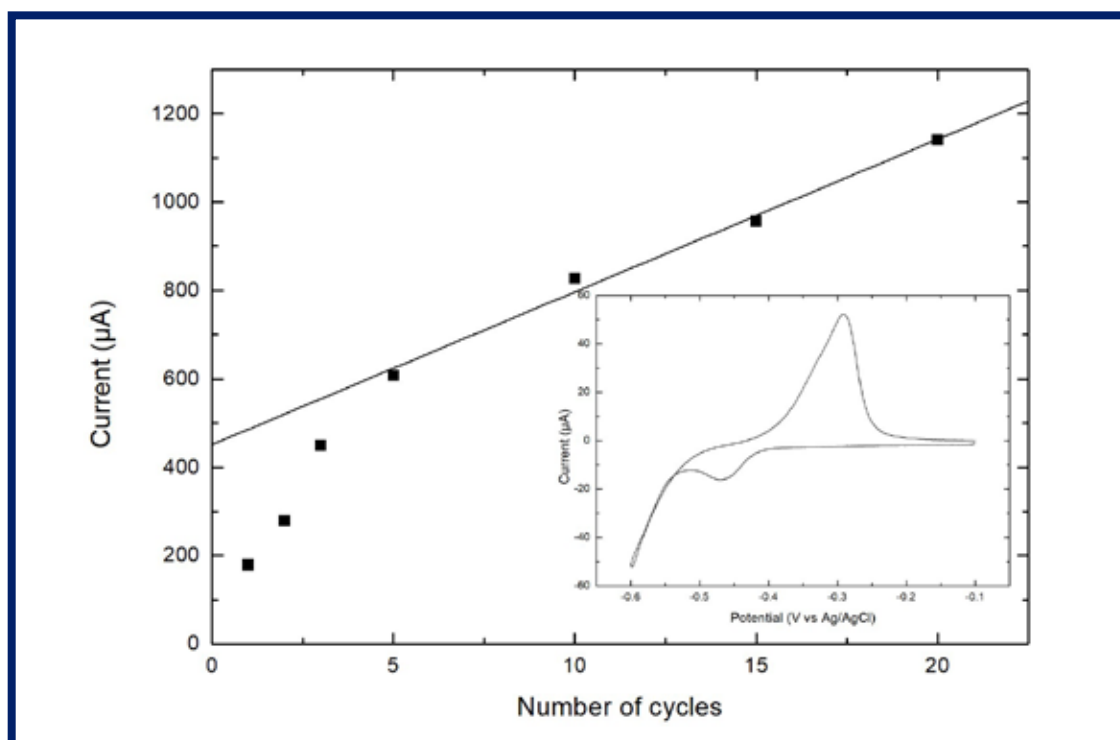


FIG. 2. Deposit growth according to the number of deposition cycles. After the first five cycles, the deposition rate becomes linear. Inset shows the cyclic voltammetry of bismuth solution on Ag/Se in which is evident the cathodic UPD peak of the metal.

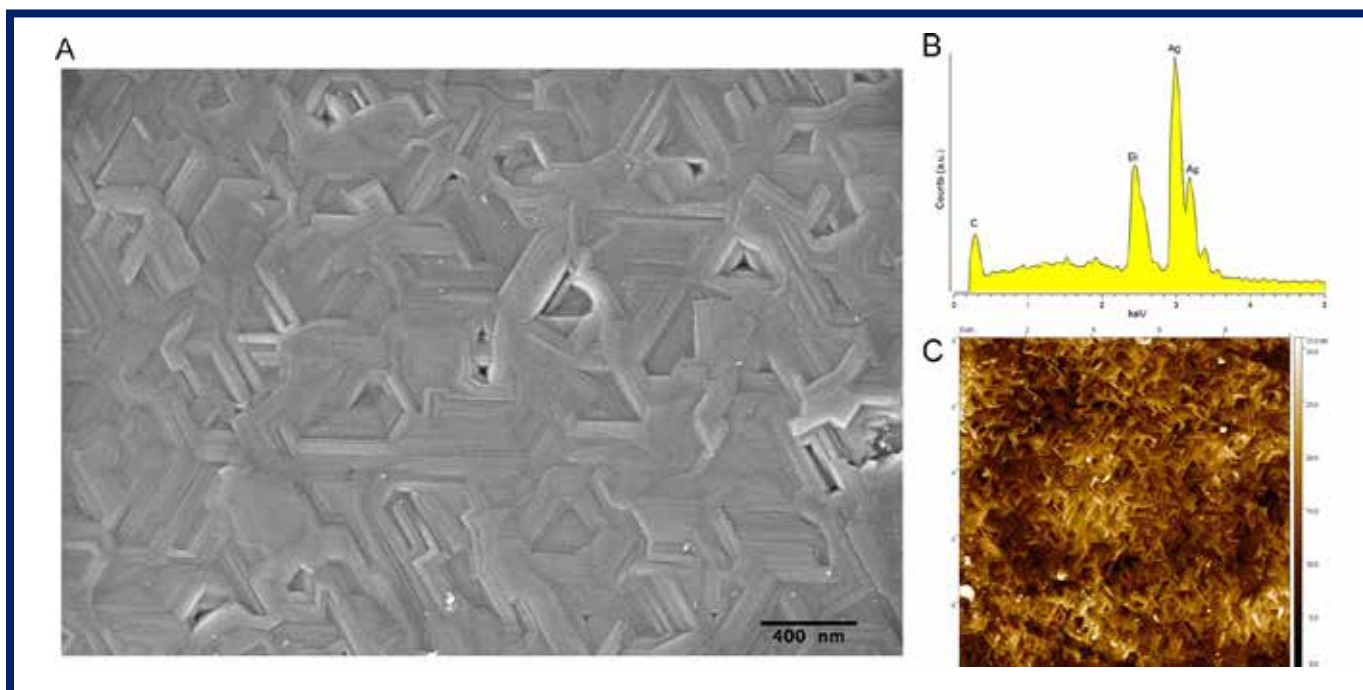


FIG. 3. A) Secondary electrons SEM image of the 50-layers bismuth sample, showing the shape and morphology of the deposit. B) EDX spectrum collected on the same area, with an accelerating voltage of 10 kV that confirms the absence of selenium. C) AFM image of the same sample.

About the Authors



WALTER GIURLANI is a PhD student of chemistry at the University of Florence. Prior to this he earned both a BS and MS in chemistry at the same university, working on the electrochemistry of electrocatalysis, energy production, and the storage of fuel cells. He is part of the

Applied Electrochemistry Group of the University of Florence Department of Chemistry. Currently he is focusing his studies on the electrodeposition and characterization of interesting materials for industrial application and next-generation technological devices. He is also collaborating with galvanic industries in R&D on the development of new deposition methods and quality control protocols for different practical applications. He may be reached at walter.giurlani@unifi.it.

<https://orcid.org/0000-0002-9949-3751>



ANDREA GIACCHERINI received his MS in chemistry in 2014 and his PhD in chemical sciences in 2018 from the University of Florence. His PhD research was focused on the characterization of ultrathin films of compound semiconductors grown by means of electrochemical atomic layer deposition (E-ALD). He is now serving as a postdoc at the University of Florence in the Department of Earth Sciences on a project aimed at finding new

solvothermal synthesis of nanostructured quaternary sulfides for photovoltaics applications. He continues to collaborate with the Department of Chemistry of the University of Florence on the characterization of new compound semiconductors deposited by means of E-ALD. He may be reached at andrea.giaccherini@unifi.it.

<https://orcid.org/0000-0003-0915-1318>



EMANUELE SALVIETTI is a temporary research fellow in the Department of Chemistry “Ugo Schiff” at the University of Florence. He received a BS in chemistry in 2004 at the same university for his work on nanostructured materials produced through electrochemistry. In 2008 he obtained his PhD in chemical science from the University of Florence, working on chemical and physical characterization on thin film by surface analysis techniques. From 2008 to 2016 he

worked on the development of colorimetric kits for food analysis and the monitoring of industrial emissions and the healthiness of workplaces. He is currently working on innovative electroplating baths and the electrodeposition of 2D materials. He may be reached at emanuele.salvietti@unifi.it.

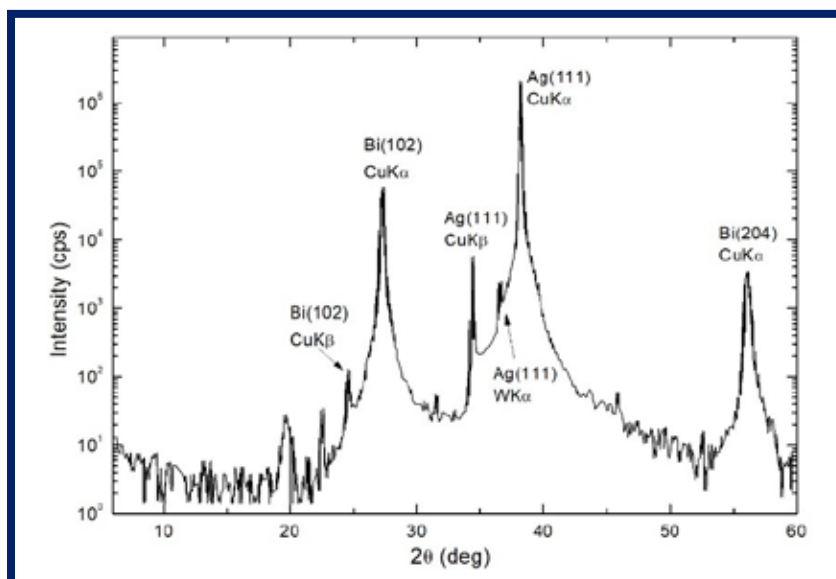


FIG. 4. XRD measurement of the 50-layers bismuth sample to prove the crystallinity of the deposit.

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MAURIZIO PASSAPONTI is a PhD student of chemistry at the University of Florence. He graduated in biology in 2011 from the same university. From 2000 to 2016 he worked as a laboratory technician in the Department of Chemistry of the University of Florence. Currently he is studying electrocatalysis for energy conversion and production in fuel cells. He is collaborating with researchers in the Applied Electrochemistry Laboratory of the Department of Chemistry on the electrodeposition of active materials for scientific and industrial purpose. In addition, he conducts collaborative studies with galvanic industries on the development and quality control of corrosion and the durability of manufactured goods. He may be reached at maurizio.passaponti@unifi.it.

<https://orcid.org/0000-0003-0931-3970>



ANDREA COMPARINI graduated with a degree in chemistry in April 2016 from the University of Florence. His bachelor's as well as his master's thesis focused on the development of green semiconductors. After graduating he became an independent collaborator at the National Interuniversity Consortium for Materials Science and Technology, where he focused on the development and characterizations of two-dimensional semiconductors through the E-ALD

technique, a low-cost and green method to produce nanostructures. Currently he serves as an R&D analyst working in the white biotech sector, developing bioproducts as bioadhesives for the wood sector. He may be reached at a.comparini@agroils.com.



VITTORIO MORANDI is the deputy director of the Bologna Unit of the CNR-IMM Institute (www.bo.imm.cnr.it), a chair and member of the committees of several international conferences, and a permanent reviewer of international projects and top-level scientific journals. He is directly involved in several national and international research projects and industrial contracts and has published more than 100 papers ($h = 24$) in international peer-reviewed journals. His main research interests concern the development of advanced electron microscopy techniques, their application to the study of nanomaterials, and the synthesis, characterization, and technological integration of graphene and graphene-based materials. He may be reached at morandi@bo.imm.cnr.it.

<https://orcid.org/0000-0002-8533-1540>



FABIOLA LISCIO is a postdoctoral fellow at CNR-IMM Bologna. She received a laurea in physics, magna cum laude, in 2005 from Roma Tre University in Rome, Italy, and received a PhD in conjunction in physics/materials science in 2009 from SIMaP-INPG in Grenoble, France. She gained experience in structural and morphological characterizations of nanostructured organic and inorganic films by means of elastic X-ray scattering techniques from a synchrotron light source. Her current research interests are focused on the role of the structure and the morphology of organic semiconductors in the optimization of their thermoelectrical properties. She may be reached at liscio@bo.imm.cnr.it.

<https://orcid.org/0000-0002-4865-1385>



MASSIMILIANO CAVALLINI is the director of research at CNR-ISMN Bologna, where he heads the multidisciplinary Nanotechnology of Multifunctional Materials Group. He received a laurea cum laude in 1995 and a PhD in chemistry in 1999 from the University of Florence. His multidisciplinary research spans unconventional bottom-up nanofabrication, applications of unconventional properties phenomena such as dewetting and polymorphism, information

storage, development of time-temperature integrators, and nanoelectrochemistry. He is the author of over 120 papers in peer-reviewed international journals and several book chapters, with an h-index of 46 and more than 5,800 citations (source: Google Scholar). He is the inventor of 15 international patents and cofounded the spin-off company Scriba Nanotecnologie Srl in 2005. He has been the principal investigator of several EU projects and received the ESF-European Yang Investigator Award in 2006. He may be reached at m.cavallini@bo.ismn.cnr.it.

<https://orcid.org/0000-0001-9802-0058>



MASSIMO INNOCENTI is the head of the Applied Electrochemistry Laboratory of the Department of Chemistry at the University of Florence. He graduated with a degree in chemistry in 1989 and is currently an associate professor of analytical chemistry. Recently he has obtained a license to serve as a full professor of analytical chemistry. His research activity is focused on nanomaterials obtainable by electrochemistry and used in the field of electrocatalysis, energy, and sensors.

Also relevant is research and industrial development in the applied galvanic field and analysis of surface to obtain many industrial contracts. Since May 2013 he has served as associate editor for the journal *Coatings*. He has been elected two times to be a member of the executive council of the Interdivisional Group on Chemistry for Renewable Energy, also known as EnerChem (2013-2018). From 2013 to 2016 he was a member of the ESRF Review Committee at the Synchrotron of Grenoble. He may be reached at minnocenti@unifi.it.

<https://orcid.org/0000-0003-1044-5583>

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